

FDME1034CZT

Complementary PowerTrench® MOSFET

N-channel: 20 V, 3.8 A, 66 mΩ P-channel: -20 V, -2.6 A, 142 mΩ

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 66 mΩ at $V_{GS} = 4.5$ V, $I_D = 3.4$ A
- Max $r_{DS(on)}$ = 86 mΩ at $V_{GS} = 2.5$ V, $I_D = 2.9$ A
- Max $r_{DS(on)}$ = 113 mΩ at $V_{GS} = 1.8$ V, $I_D = 2.5$ A
- Max $r_{DS(on)}$ = 160 mΩ at $V_{GS} = 1.5$ V, $I_D = 2.1$ A

Q2: P-Channel

- Max $r_{DS(on)}$ = 142 mΩ at $V_{GS} = -4.5$ V, $I_D = -2.3$ A
- Max $r_{DS(on)}$ = 213 mΩ at $V_{GS} = -2.5$ V, $I_D = -1.8$ A
- Max $r_{DS(on)}$ = 331 mΩ at $V_{GS} = -1.8$ V, $I_D = -1.5$ A
- Max $r_{DS(on)}$ = 530 mΩ at $V_{GS} = -1.5$ V, $I_D = -1.2$ A

- Low profile: 0.55 mm maximum in the new package MicroFET 1.6x1.6 Thin

- Free from halogenated compounds and antimony oxides

- HBM ESD protection level > 1600 V (Note 3)

- RoHS Compliant



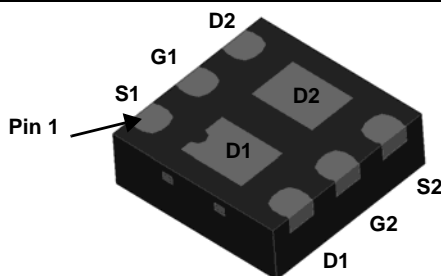
General Description

This device is designed specifically as a single package solution for a DC/DC 'Switching' MOSFET in cellular handset and other ultra-portable applications. It features an independent N-Channel & P-Channel MOSFET with low on-state resistance for minimum conduction losses. The gate charge of each MOSFET is also minimized to allow high frequency switching directly from the controlling device.

The MicroFET 1.6x1.6 Thin package offers exceptional thermal performance for its physical size and is well suited to switching and linear mode applications.

Applications

- DC-DC Conversion
- Level Shifted Load Switch

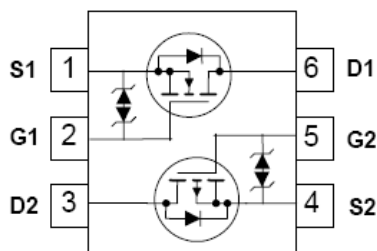


BOTTOM



TOP

MicroFET 1.6x1.6 Thin



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Q1	Q2	Units
V _{DS}	Drain to Source Voltage	20	-20	V
V _{GS}	Gate to Source Voltage	±8	±8	V
I _D	Drain Current -Continuous T _A = 25 °C (Note 1a)	3.8	-2.6	A
	-Pulsed	6	-6	
P _D	Power Dissipation for Single Operation T _A = 25 °C (Note 1a)	1.4		W
	Power Dissipation for Single Operation T _A = 25 °C (Note 1b)	0.6		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Single Operation) (Note 1a)	90	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Single Operation) (Note 1b)	195	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
5T	FDME1034CZT	MicroFET 1.6x1.6 Thin	7"	8 mm	5000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$ $I_D = -250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	Q1 Q2	20 -20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$ $I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$	Q1 Q2		16 -12		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}$, $V_{GS} = 0\text{ V}$ $V_{DS} = -16\text{ V}$, $V_{GS} = 0\text{ V}$	Q1 Q2			1 -1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}$, $V_{DS} = 0\text{ V}$	All			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$ $V_{GS} = V_{DS}$, $I_D = -250\text{ }\mu\text{A}$	Q1 Q2	0.4 -0.4	0.7 -0.6	1.0 -1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$	Q1 Q2		-3 2		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5\text{ V}$, $I_D = 3.4\text{ A}$	Q1		55	66	m Ω
		$V_{GS} = 2.5\text{ V}$, $I_D = 2.9\text{ A}$			68	86	
		$V_{GS} = 1.8\text{ V}$, $I_D = 2.5\text{ A}$			85	113	
		$V_{GS} = 1.5\text{ V}$, $I_D = 2.1\text{ A}$			106	160	
		$V_{GS} = 4.5\text{ V}$, $I_D = 3.4\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$			76	112	
		$V_{GS} = -4.5\text{ V}$, $I_D = -2.3\text{ A}$	Q2		95	142	
		$V_{GS} = -2.5\text{ V}$, $I_D = -1.8\text{ A}$			120	213	
		$V_{GS} = -1.8\text{ V}$, $I_D = -1.5\text{ A}$			150	331	
		$V_{GS} = -1.5\text{ V}$, $I_D = -1.2\text{ A}$			190	530	
		$V_{GS} = -4.5\text{ V}$, $I_D = -2.3\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$			128	190	
g_{FS}	Forward Transconductance	$V_{DS} = 4.5\text{ V}$, $I_D = 3.4\text{ A}$ $V_{DS} = -4.5\text{ V}$, $I_D = -2.3\text{ A}$	Q1 Q2		9 7		S

Dynamic Characteristics

C_{iss}	Input Capacitance	Q1	Q1 Q2		225 305	300 405	pF
C_{oss}	Output Capacitance	$V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		40 55	55 75	pF
C_{rss}	Reverse Transfer Capacitance	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		25 50	40 75	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	Q1	Q1 Q2		4.5 4.7	10 10	ns
t_r	Rise Time	$V_{DD} = 10\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		2.0 4.8	10 10	
$t_{d(off)}$	Turn-Off Delay Time	Q2	Q1 Q2		15 33	27 53	
t_f	Fall Time	$V_{DD} = -10\text{ V}$, $I_D = -1\text{ A}$, $V_{GS} = -4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		1.7 16	10 29	
Q_g	Total Gate Charge	Q1	Q1 Q2		3 5.5	4.2 7.7	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 10\text{ V}$, $I_D = 3.4\text{ A}$, $V_{GS} = 4.5\text{ V}$	Q1 Q2		0.4 0.6		
Q_{gd}	Gate to Drain "Miller" Charge	$V_{DD} = -10\text{ V}$, $I_D = -2.3\text{ A}$, $V_{GS} = -4.5\text{ V}$	Q1 Q2		0.6 1.4		

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

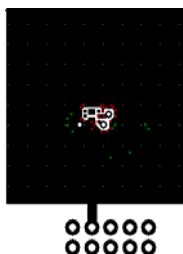
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
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Drain-Source Diode Characteristics

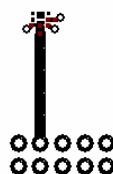
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 0.9\text{ A}$ (Note 2)	Q1		0.7	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = -0.9\text{ A}$ (Note 2)	Q2		-0.8	-1.2	
t_{rr}	Reverse Recovery Time	Q1 $I_F = 3.4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{S}$	Q1		8.5	17	ns
			Q2		16	29	
Q_{rr}	Reverse Recovery Time	Q2 $I_F = -2.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{S}$	Q1		1.4	10	nC
			Q2		4.4	10	

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 90 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 195 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

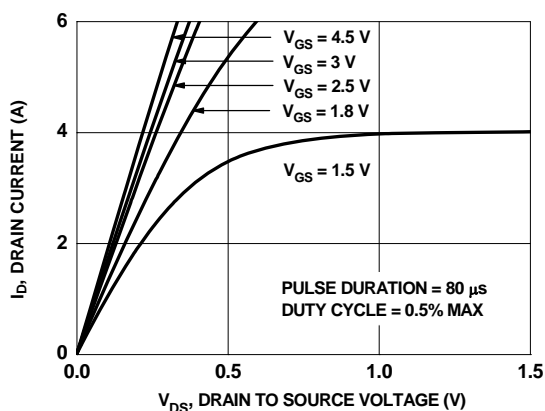


Figure 1. On Region Characteristics

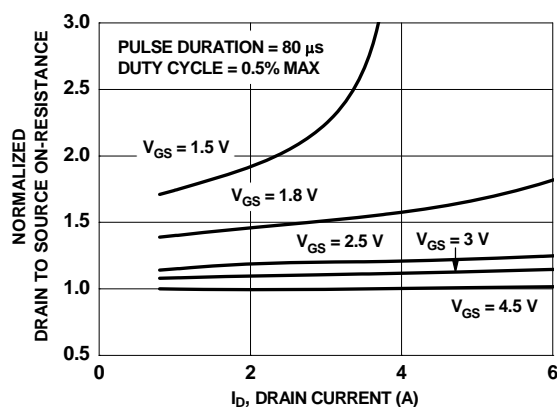


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

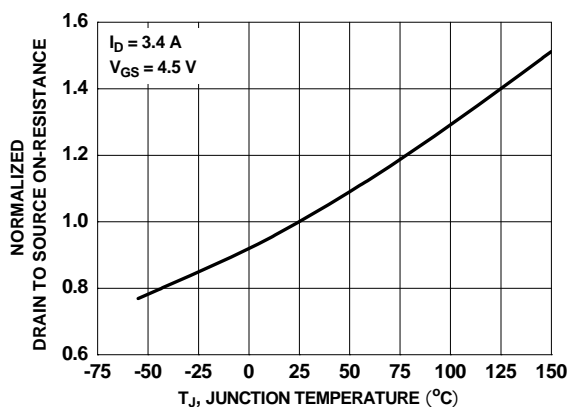


Figure 3. Normalized On Resistance vs Junction Temperature

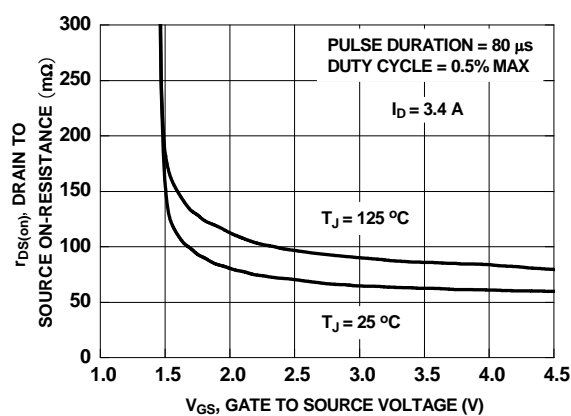


Figure 4. On-Resistance vs Gate to Source Voltage

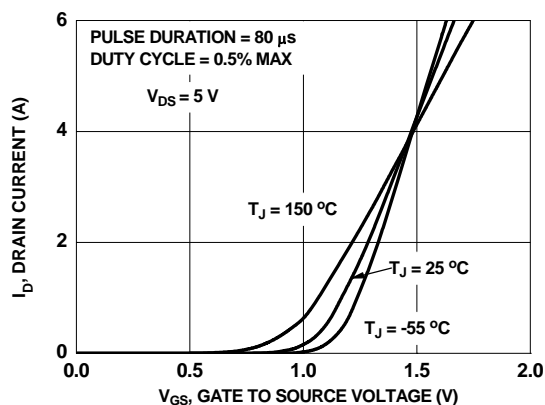


Figure 5. Transfer Characteristics

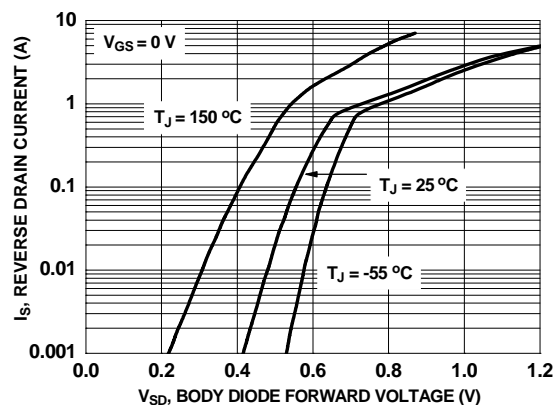


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

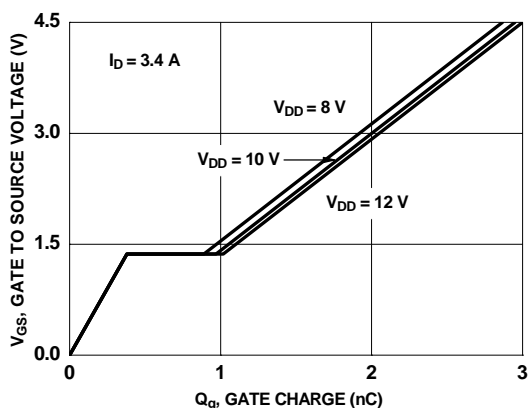


Figure 7. Gate Charge Characteristics

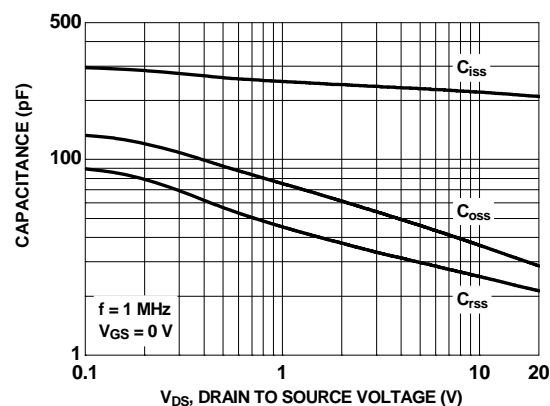


Figure 8. Capacitance vs Drain to Source Voltage

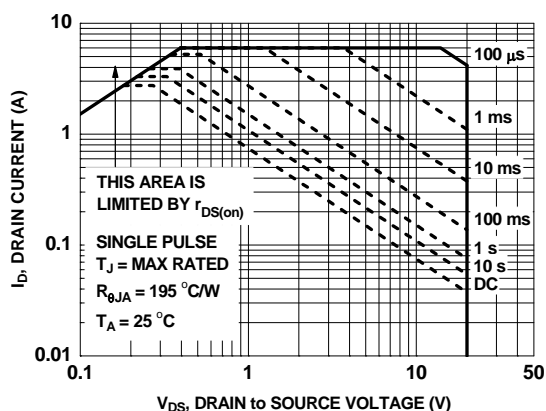


Figure 9. Forward Bias Safe Operating Area

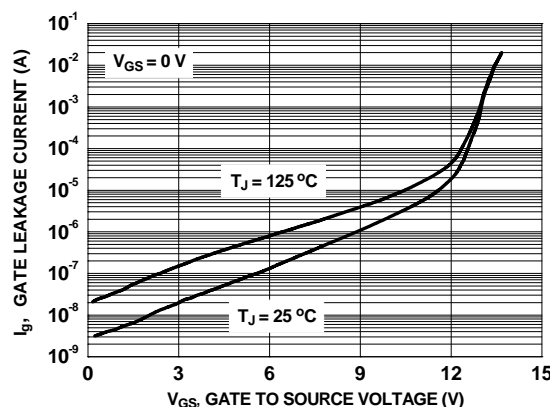


Figure 10. Gate Leakage Current vs Gate to Source Voltage

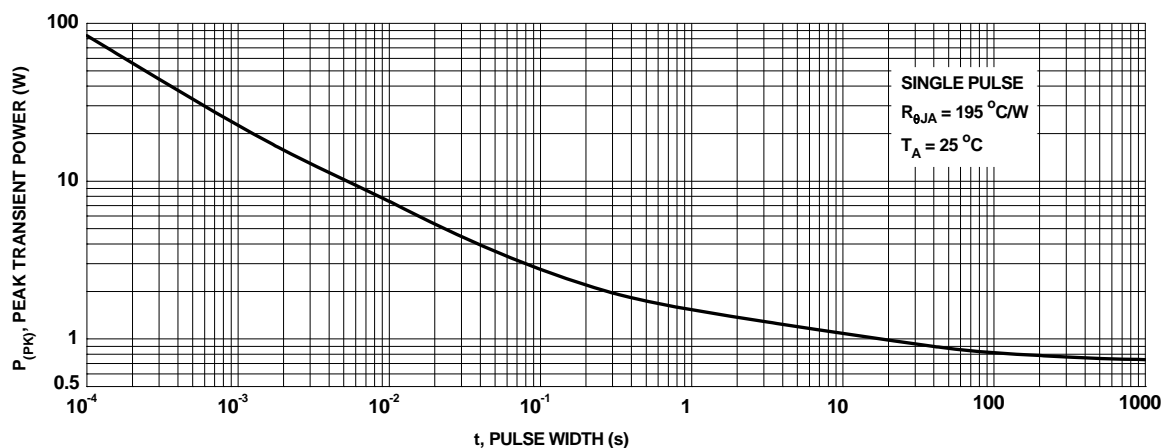


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

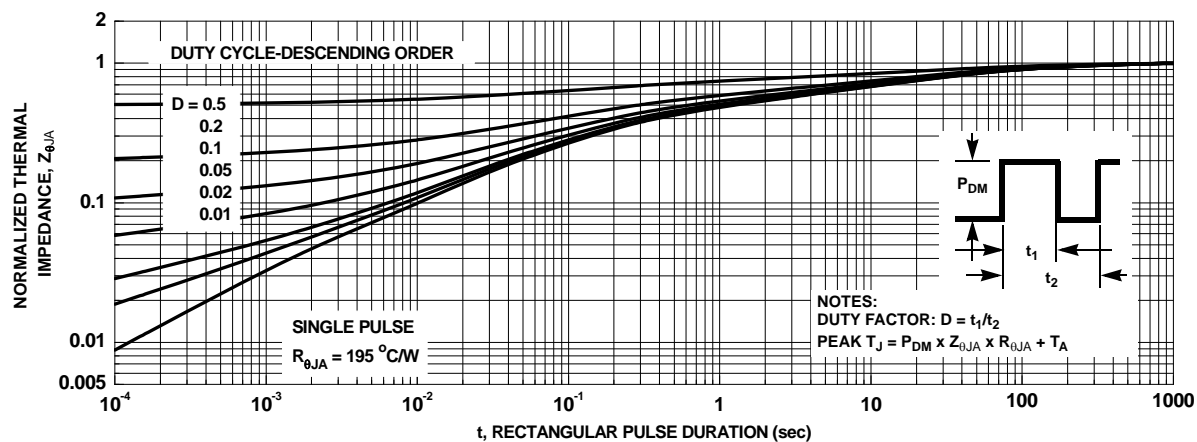


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (Q2 P-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

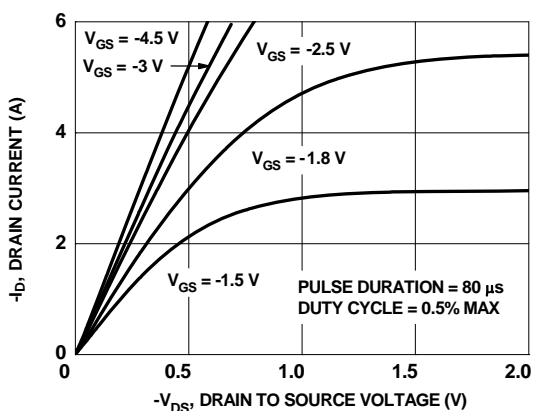


Figure 13. On-Region Characteristics

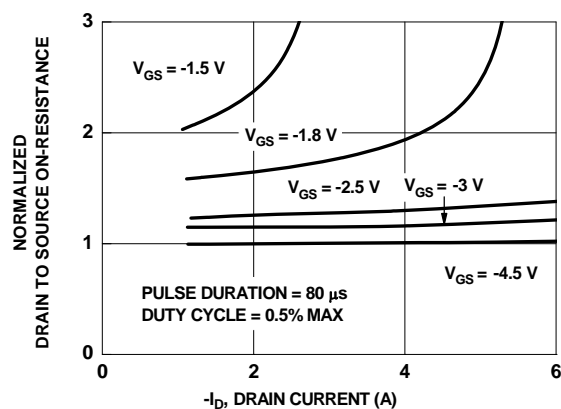


Figure 14. Normalized on-Resistance vs Drain Current and Gate Voltage

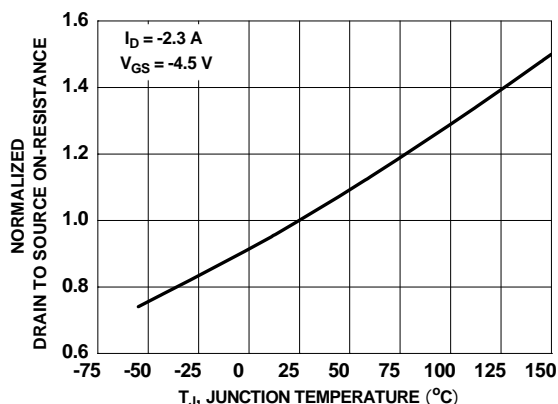


Figure 15. Normalized On-Resistance vs Junction Temperature

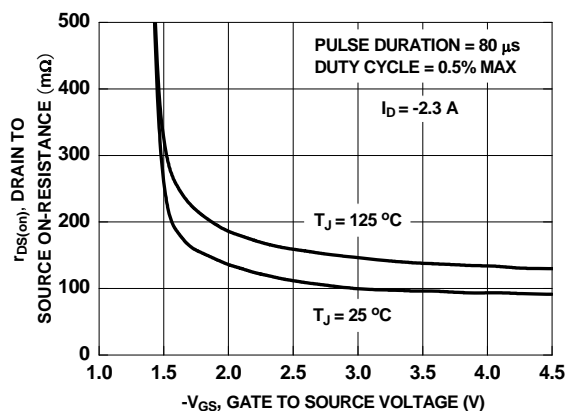


Figure 16. On-Resistance vs Gate to Source Voltage

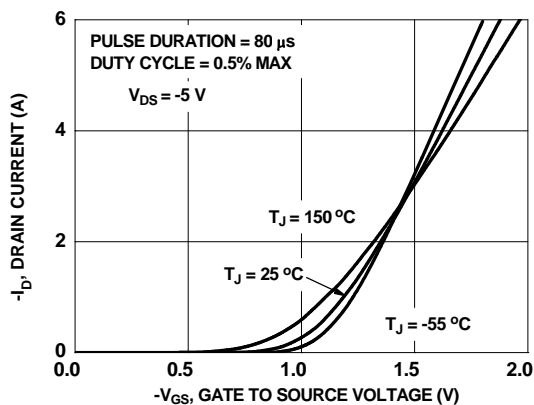


Figure 17. Transfer Characteristics

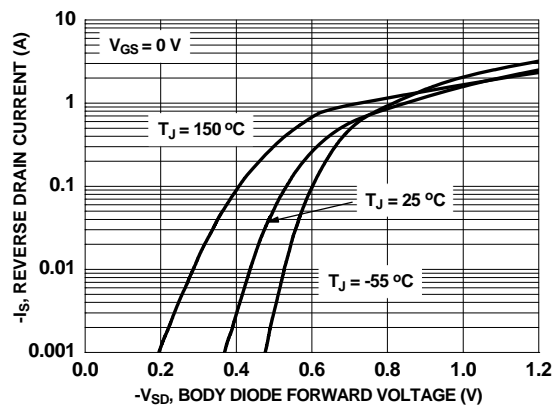


Figure 18. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q2 P-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted

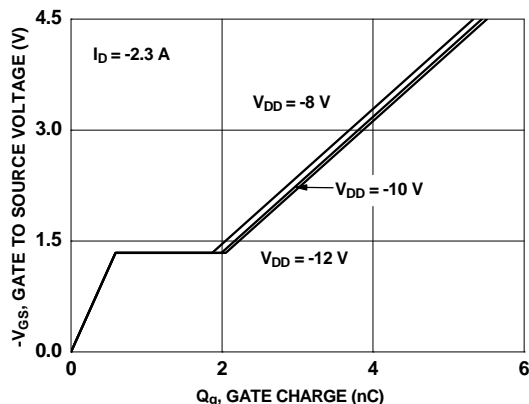


Figure 19. Gate Charge Characteristics

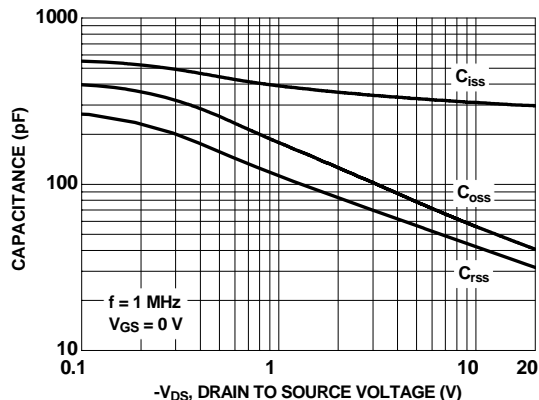


Figure 20. Capacitance vs Drain to Source Voltage

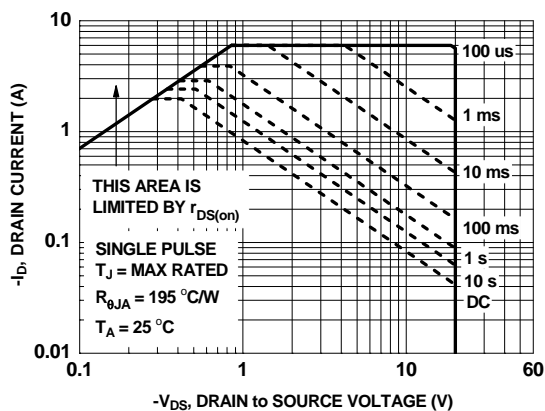


Figure 21. Forward Bias Safe Operating Area

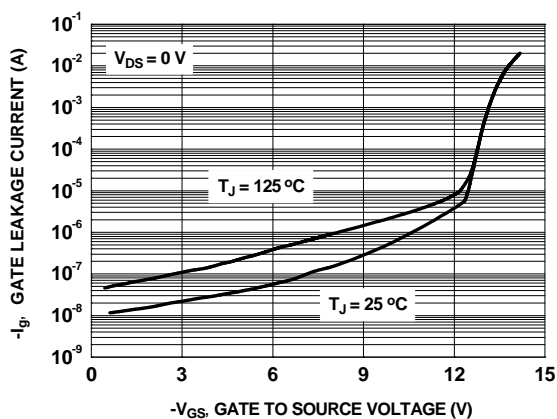


Figure 22. Gate Leakage Current vs Gate to Source Voltage

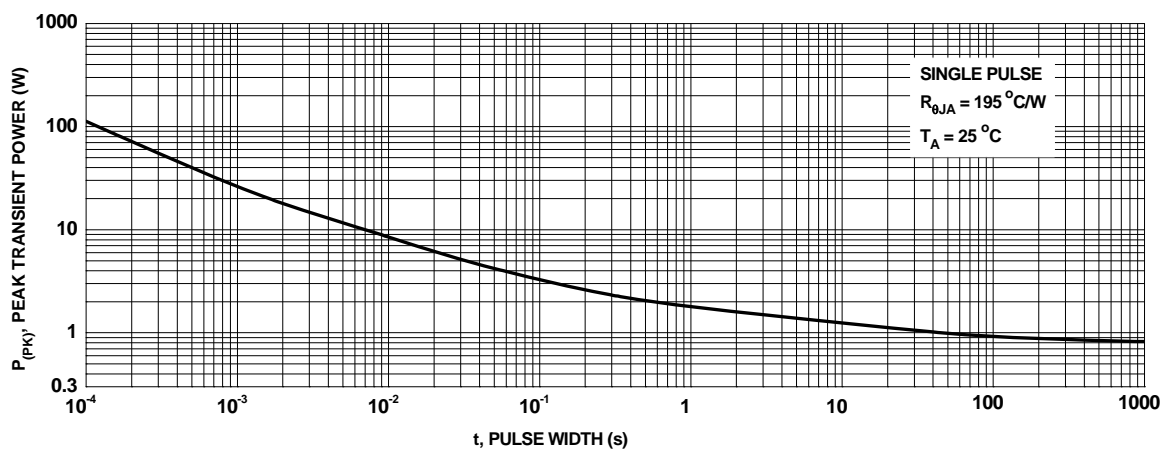
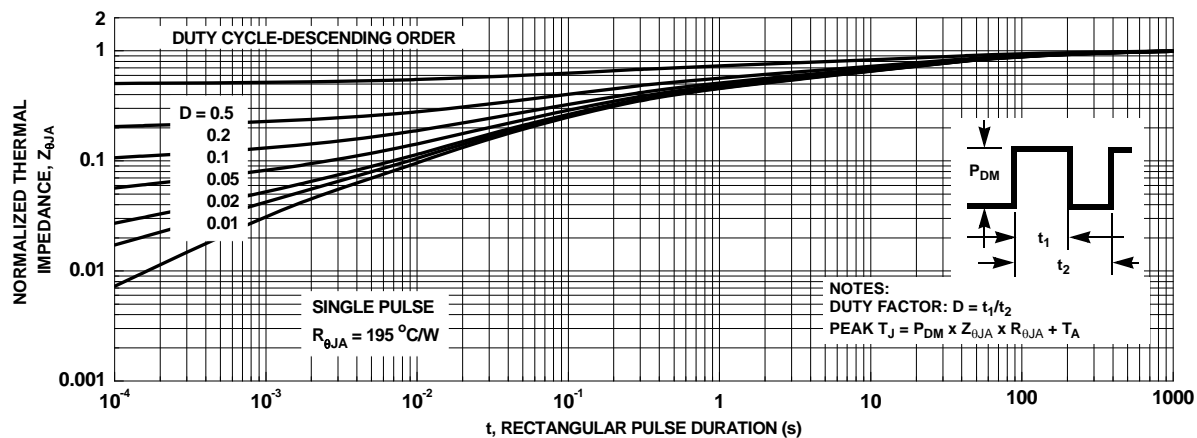
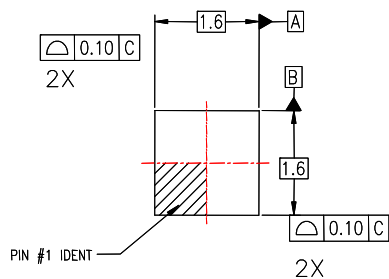


Fig 23. Single Pulse Maximum Power Dissipation

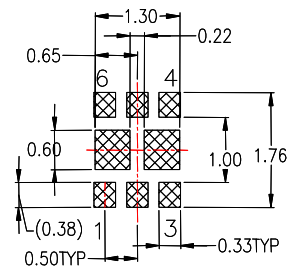
Typical Characteristics (Q2 P-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted



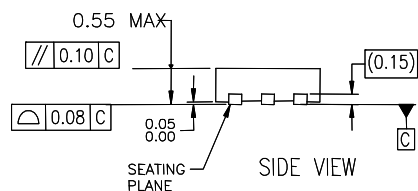
Dimensional Outline and Pad Layout



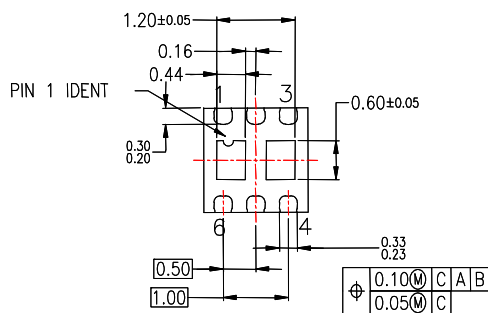
TOP VIEW



RECOMMENDED LAND PATTERN



SIDE VIEW



BOTTOM VIEW



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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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